

METHOD FOR DETERMINING PHOTORESIST THICKNESS AND
STRUCTURE FORMED USING DETERMINED PHOTORESIST
THICKNESS

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ABSTRACT OF THE DISCLOSURE

A method for determining photoresist thickness is disclosed that can be used in a semiconductor fabrication process. A layer of material is formed
10 that has one or more common characteristic relative to the material in the layer that is to be patterned in the semiconductor fabrication process. A layer of photoresist is then formed that has varying thickness. The thickness of the layer of photoresist is determined at a plurality of different points. The layer of photoresist is exposed, developed and etched. The remaining structures are
15 then analyzed to determine photoresist thickness to be used in the semiconductor fabrication process. The determined photoresist thickness is then used in the semiconductor fabrication process to form structures on a semiconductor wafer.